Low V_F Silicon Power Schottky Diode

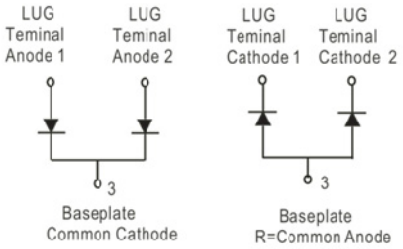
V_{RRM} = 30 V

$I_{F(AV)}$ = 600 A

Features

- High Surge Capability
- Type 30 V V_{RRM}
- Not ESD Sensitive

Twin Tower Package





RoHS COMPLIANT

REACH COMPLIANCE

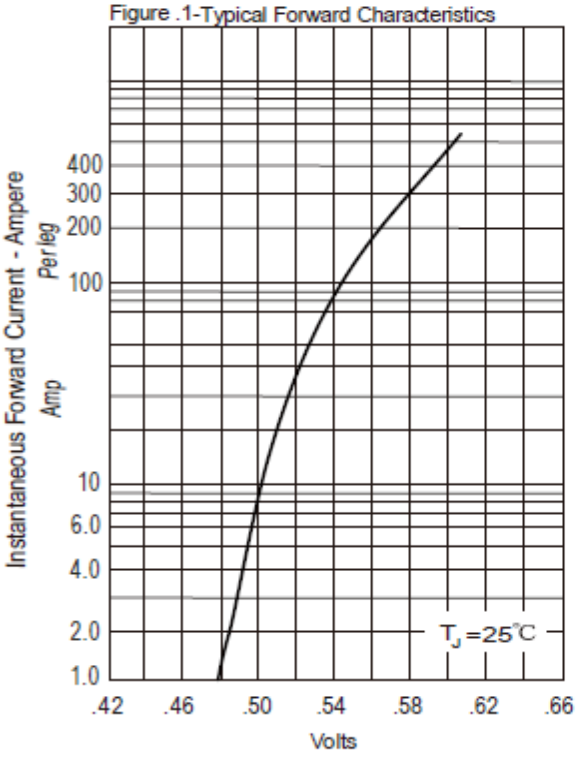
Maximum ratings, at T_j = 25 °C, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBR60030CT(R)L	Unit
Maximum recurrent peak reverse voltage	V_{RRM}		30	V
Maximum RMS voltage	V_{RMS}		21	V
Maximum DC blocking voltage	V_{DC}		30	V
Operating temperature	T_j		-55 to 150	°C
Storage temperature	T_{stg}		-55 to 150	°C

Electrical characteristics, at Tj = 25 °C, unless otherwise specified

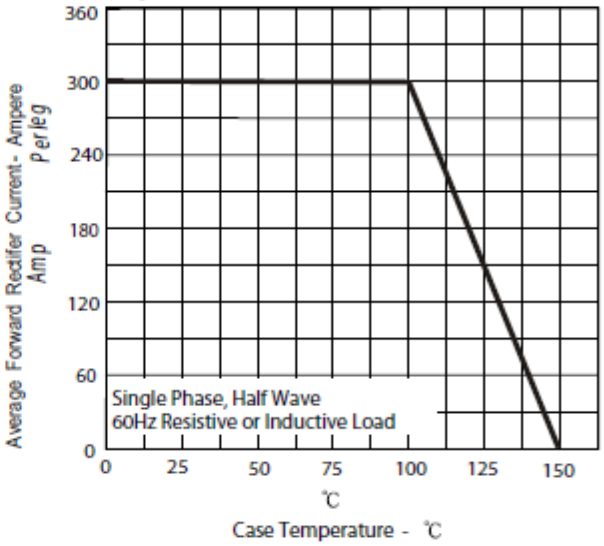
Parameter	Symbol	Conditions	MBR60030CT(R)L	Unit
Average forward current (per pkg)	$I_{F(AV)}$	T_C = 100 °C	600	A
Peak forward surge current (per leg)	I_{FSM}	t_p = 8.3 ms, half sine	4000	A
Maximum instantaneous forward voltage (per leg)	V_F	I_{FM} = 300 A, Tj = 25 °C	0.58	V
Maximum instantaneous reverse current at rated DC blocking voltage (per leg)	I_R	T_j = 25 °C T_j = 100 °C	3 250	mA
Thermal characteristics				
Maximum thermal resistance, junction - case (per leg)	$R_{\Theta JC}$		0.28	°C/W

Figure .1-Typical Forward Characteristics



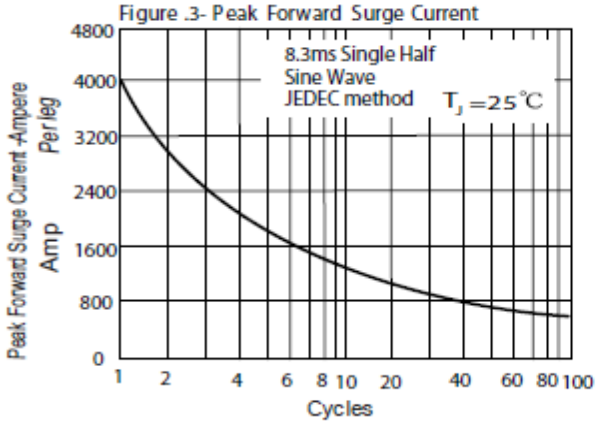
Instantaneous Forward Voltage - Volts

Figure .2- Forward Derating Curve



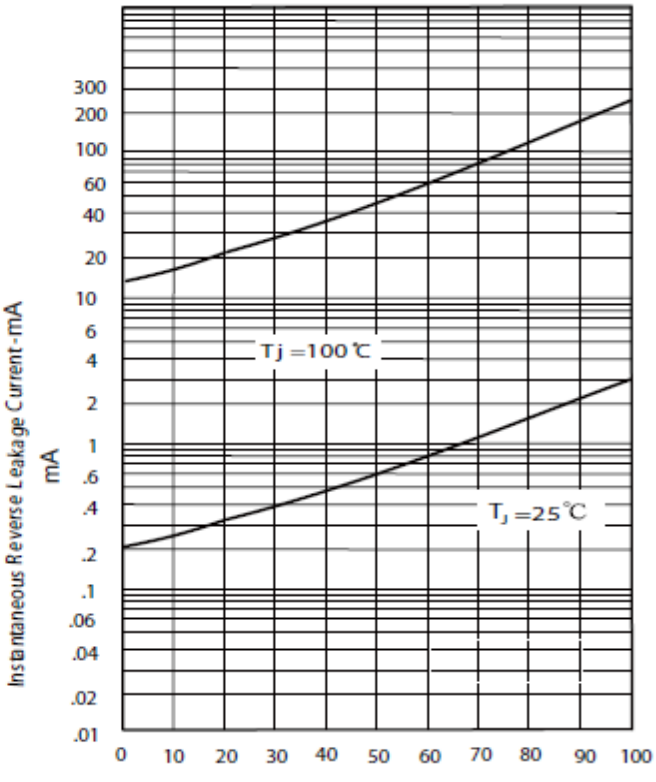
Case Temperature - ℃

Figure .3- Peak Forward Surge Current



Number Of Cycles At 60Hz - Cycles

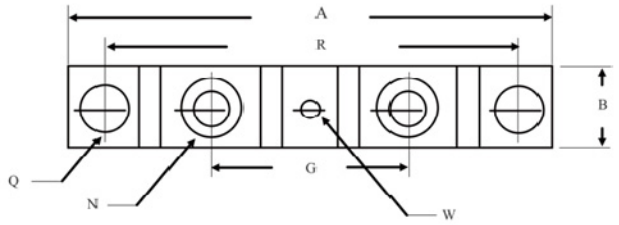
Figure .4- Typical Reverse Characteristics

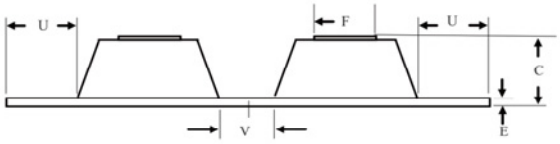


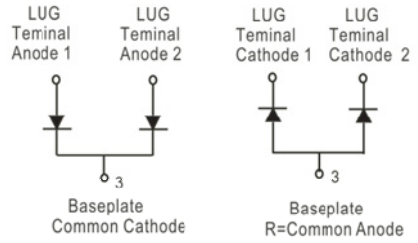
Reverse Voltage - Volts(%)

Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.







DIM	Inches		Millimeters	
	Min	Max	Min	Max
A	-----	3.630	-----	92.40
B	0.700	0.800	17.78	20.32
C	-----	0.650	-----	16.51
E	0.130	0.141	3.30	3.60
F	0.482	0.490	12.25	12.45
G	1.368	BSC	34.75	BSC
N	1/4-20 UNC FULL			
Q	0.275	0.290	6.99	7.37
R	3.150	BSC	80.01	BSC
U	0.600	-----	15.24	-----
V	0.312	0.370	7.92	9.40
W	0.180	0.195	4.57	4.95